

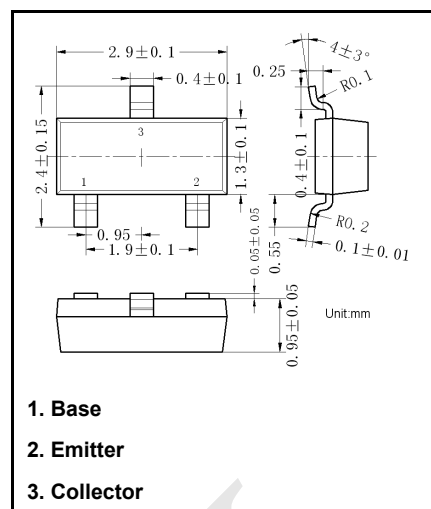
SOT-23 Plastic-Encapsulate Transistors

S8550 PNP Transistors

Features

- Complimentary to S8050
- Collector current: $I_C=0.8A$

Marking: 2TY



Maximum Ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	-40	V
V_{CEO}	Collector Emitter Voltage	-25	V
V_{EBO}	Emitter Base Voltage	-5	V
I_C	Collector Current	-0.8	A
P_C	Collector Power Dissipation	300	mW
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55 ~ +150	$^{\circ}C$

Electrical Characteristics ($T_a=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100\mu A, I_E = 0$	-40			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10mA, I_B = 0$	-25			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -100\mu A, I_C = 0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB} = -40V, I_E = 0$	-100			nA
I_{CEO}	Collector cut-off current	$V_{CE} = -20V, I_B = 0$	-100			nA
I_{EBO}	Emitter cut-off current	$V_{EB} = -3V, I_C = 0$	-100			nA
$h_{FE(1)}$	DC current gain	$V_{CE} = -1V, I_C = -50mA$	160		320	
$h_{FE(2)}$		$V_{CE} = -1V, I_C = -500mA$	50			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = -500mA, I_B = -50mA$			-0.6	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C = -500mA, I_B = -50mA$			-1.2	V
f_T	Transition frequency	$V_{CE} = -6V, I_C = -20mA, f = 30MHz$	150			MHz

Typical Characteristics

